NEW PRODUCT

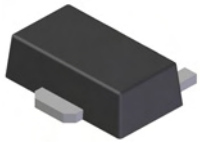
DCX68/-25

NPN SURFACE MOUNT TRANSISTOR

Please click here to visit our online spice models database.

Features

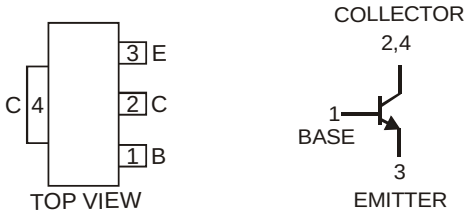
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DCX69)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	1.0	A
Peak Pulse Current	I_{CM}	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T_A = 25°C	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T_A = 25°C	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)							
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	25	—	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	20	—	—	V	I_C = 10mA, I_B = 0
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	5.0	—	—	V	I_E = 100μA, I_C = 0
Collector-Base Cutoff Current		I_{CBO}	—	—	0.1 10	μA	V_{CB} = 25V, I_E = 0 V_{CB} = 25V, I_E = 0, T_A = 150°C
Emitter-Base Cutoff Current		I_{EBO}	—	—	10	μA	V_{EB} = 5.0V, I_C = 0
ON CHARACTERISTICS (Note 4)							
DC Current Gain	DCX68, DCX68-25	h_{FE}	50 60	—	— —	—	V_{CE} = 10V, I_C = 5.0mA V_{CE} = 1.0V, I_C = 1.0A
	DCX68		85		375		V_{CE} = 1.0V, I_C = 500mA
	DCX68-25		160		375		V_{CE} = 1.0V, I_C = 500mA
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	—	—	0.5	V	I_C = 1.0A, I_B = 100mA
Base-Emitter Turn-On Voltage		$V_{BE(ON)}$	—	—	1.0	V	I_C = 1.0A, V_{CE} = 1.0V
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f_T	—	330	—	MHz	V_{CE} = 5.0V, I_C = 100mA, f = 100MHz
Output Capacitance		C_{obo}	—	—	25	pF	V_{CB} = 10V, I_E = 0, f = 1MHz

Notes:
1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

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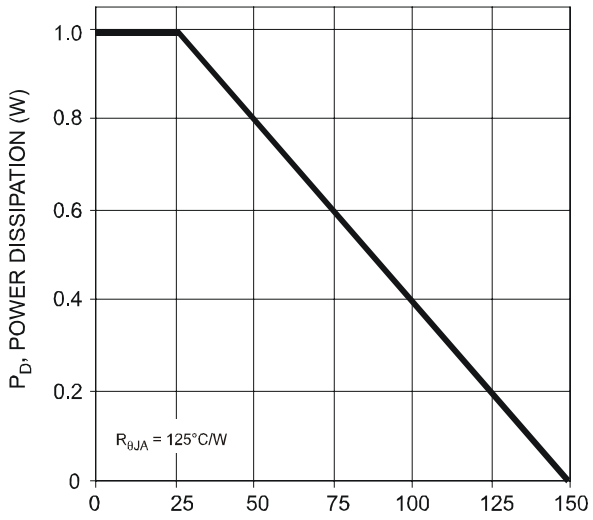

Fig. 1 Power Dissipation vs. Ambient Temperature

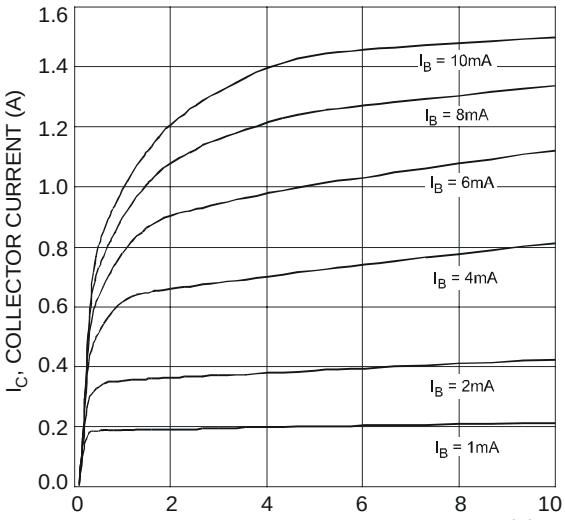

Fig. 2 Typical Collector Current vs. Collector Emitter Voltage

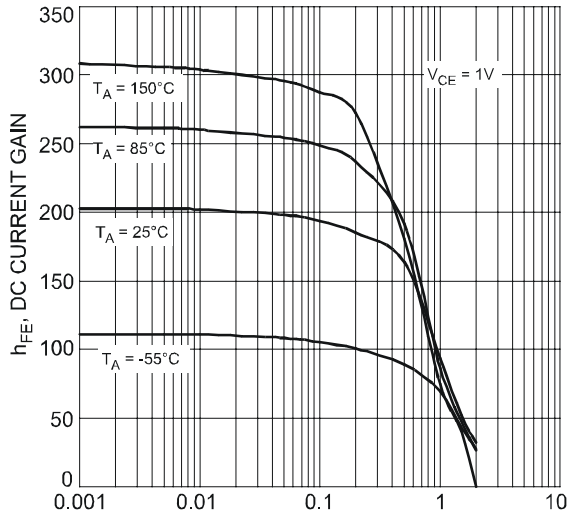

Fig. 3 Typical DC Current Gain vs. Collector Current (DCP68)

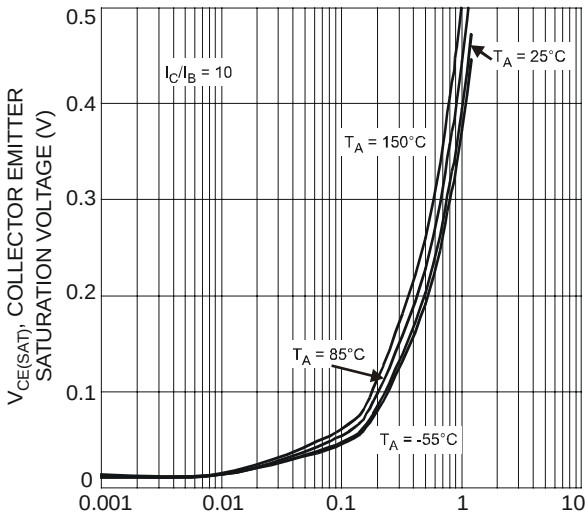

Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

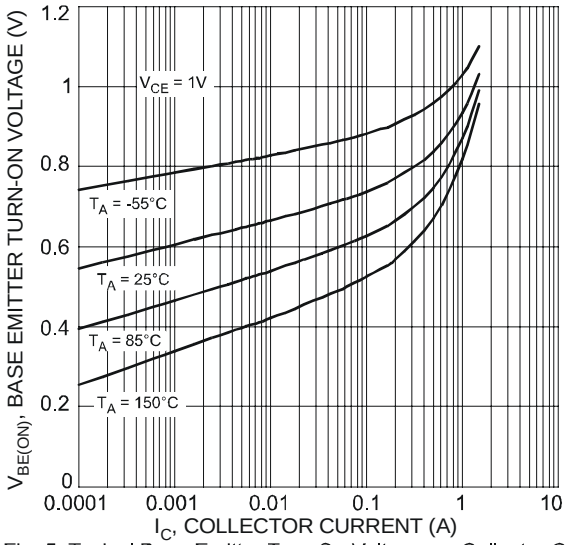

Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current

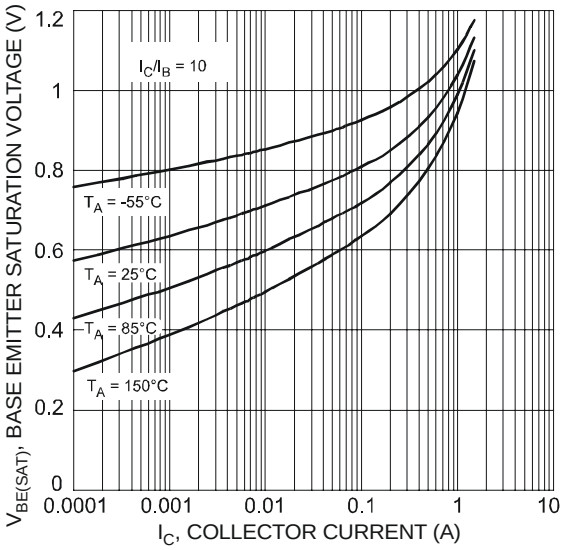

Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current

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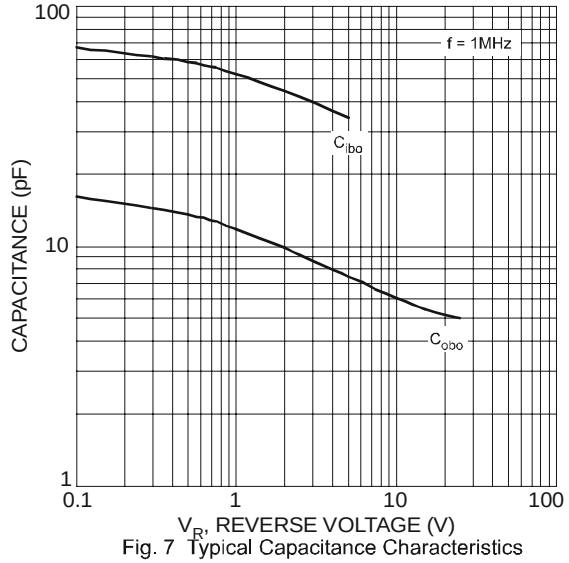


Fig. 7 Typical Capacitance Characteristics

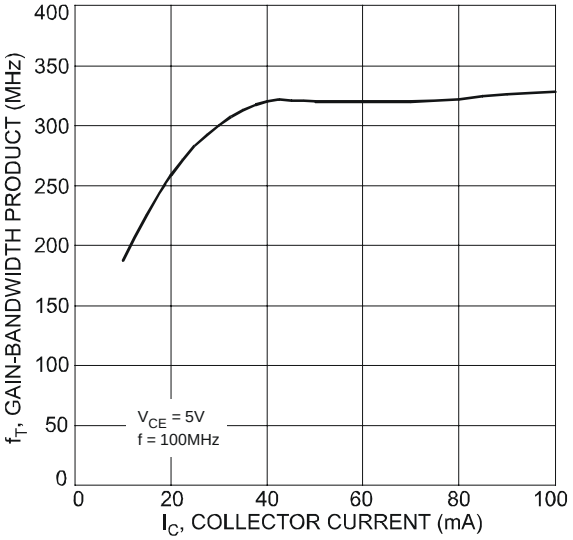


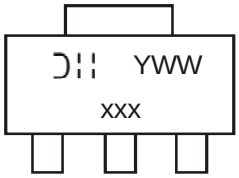
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DCX68-13	SOT89-3L	2500/Tape & Reel
DCX68-25-13	SOT89-3L	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

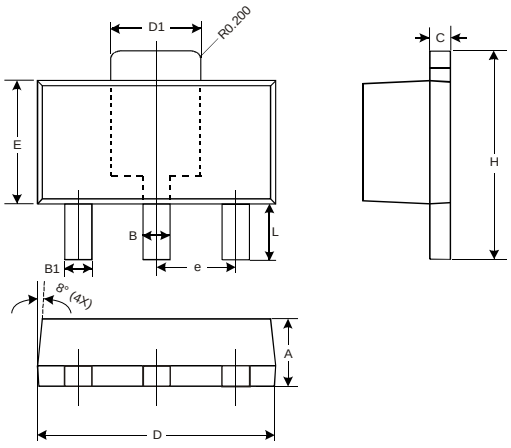
Marking Information



(Top View)

xxx = Product Type Marking Code:
N12 = DCX68
N12-25 = DCX68-25
YWW = Date Code Marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

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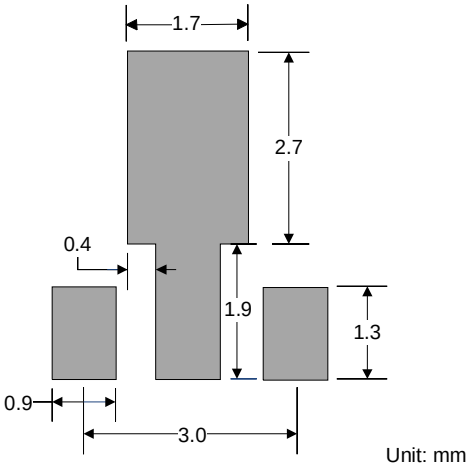
Suggested Pad Layout



Unit: mm

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